



# STB200N6F3, STI200N6F3 STP200N6F3

N-channel 60 V, 3 mΩ, 120 A D<sup>2</sup>PAK, TO-220, I<sup>2</sup>PAK  
STripFET™ Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>	P <sub>w</sub>
STB200N6F3	60 V	< 3.5 mΩ	120 A <sup>(1)</sup>	330 W
STI200N6F3	60 V	< 3.8 mΩ	120 A <sup>(1)</sup>	330 W
STP200N6F3	60 V	< 3.8 mΩ	120 A <sup>(1)</sup>	330 W

1. Value limited by wire bonding

- Ultra low on-resistance
- 100% avalanche tested

## Application

- Switching applications

## Description

This STripFET™ III Power MOSFET technology is among the latest improvements, which have been especially tailored to minimize on-state resistance providing superior switching performance.

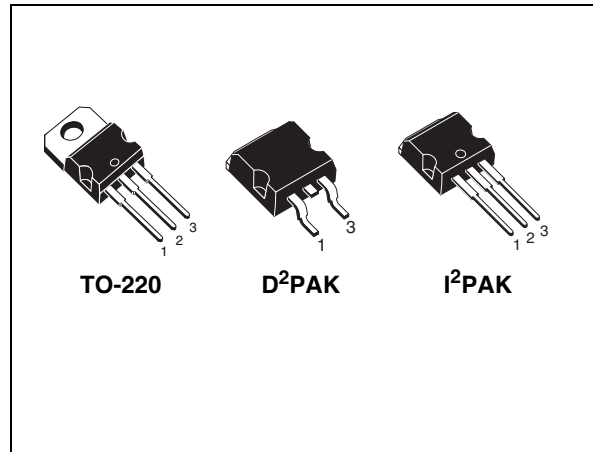


Figure 1. Internal schematic diagram

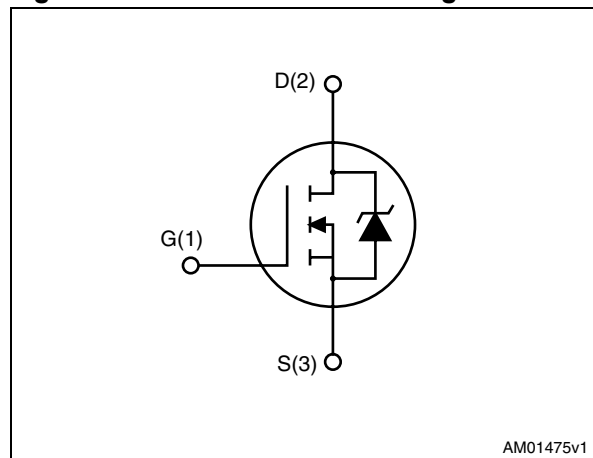


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB200N6F3	200N6F3	D <sup>2</sup> PAK	Tape and reel
STI200N6F3	200N6F3	I <sup>2</sup> PAK	Tube
STP200N6F3	200N6F3	TO-220	Tube

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS}=0$ )	60	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C=100^\circ\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	480	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	330	W
	Derating factor	2.2	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	918	mJ
$T_j$ $T_{stg}$	Operating junction temperature storage temperature	-55 To 175	$^\circ\text{C}$

1. Current limited by package.
2. Pulse width limited by safe operating area.
3. Starting  $T_j = 25^\circ\text{C}$ ,  $I_D = 60\text{ A}$ ,  $V_{DD} = 35\text{ V}$  (see [Figure 18](#) and [Figure 19](#))

**Table 3. Thermal data**

Symbol	Parameter	TO-220/l <sup>2</sup> PAK	D <sup>2</sup> PAK	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.45		$^\circ\text{C}/\text{W}$
$R_{thj-a}$	Thermal resistance junction-ambient max	62.5		$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient max		50	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300		$^\circ\text{C}$

1. When mounted on 1 inch<sup>2</sup> FR4 2oz Cu.

## 2 Electrical characteristics

( $T_{CASE}=25\text{ °C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0$	60			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{max rating}$ , $V_{DS} = \text{max rating}$ , @ $125\text{°C}$			10 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\ \text{V}$			$\pm 200$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\ \text{V}$ , $I_D = 60\ \text{A}$ <b>D<sup>2</sup>PAK</b> <b>TO-220, I<sup>2</sup>PAK</b>		3 3.3	3.5 3.8	$\text{m}\Omega$ $\text{m}\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\ \text{V}$ , $f = 1\ \text{MHz}$ , $V_{GS} = 0$	-	6265	-	pF
$C_{oss}$	Output capacitance			1295		pF
$C_{rss}$	Reverse transfer capacitance			43		pF
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30\ \text{V}$ , $I_D = 60\ \text{A}$ $R_G = 4.7\ \Omega$ , $V_{GS} = 10\ \text{V}$ <i>(see Figure 15, Figure 20)</i>	-	26	-	ns
$t_r$	Rise time			75		ns
$t_{d(off)}$	Turn-off delay time			86		ns
$t_f$	Fall time			14		ns
$Q_g$	Total gate charge	$V_{DD} = 30\ \text{V}$ , $I_D = 120\ \text{A}$ , $V_{GS} = 10\ \text{V}$ , <i>(see Figure 16)</i>	-	101	-	nC
$Q_{gs}$	Gate-source charge			36		nC
$Q_{gd}$	Gate-drain charge			25.2		nC

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		120 480	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=120\text{ A}$ , $V_{GS}=0$	-		1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=120\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=48\text{ V}$ , $T_j=150\text{ }^\circ\text{C}$ (see <a href="#">Figure 17</a> )	-	67 177.6 5.3		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, I<sup>2</sup>PAK

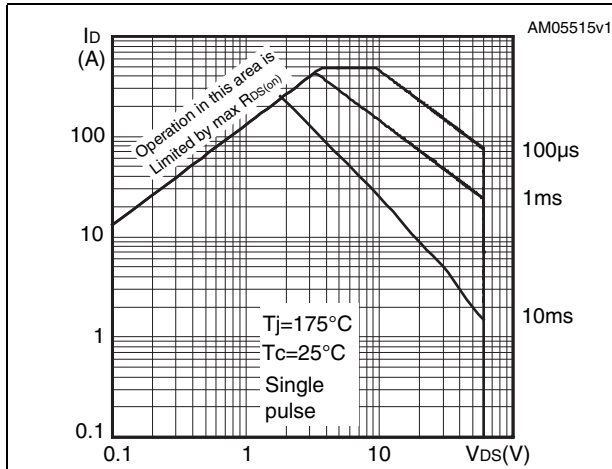


Figure 3. Thermal impedance for TO-220, I<sup>2</sup>PAK

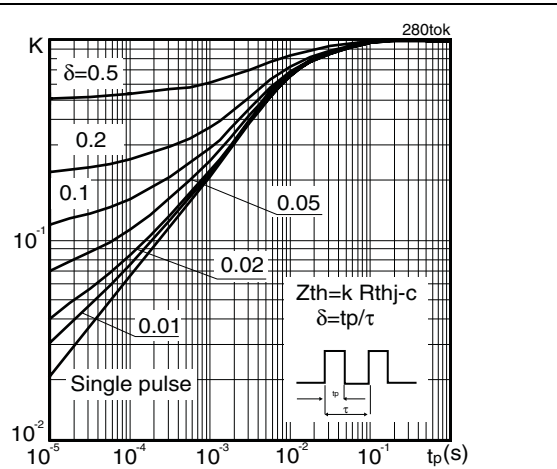


Figure 4. Safe operating area for D<sup>2</sup>PAK

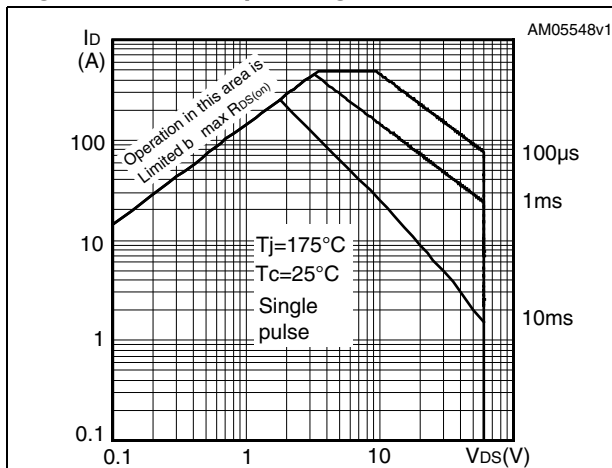


Figure 5. Thermal impedance for D<sup>2</sup>PAK

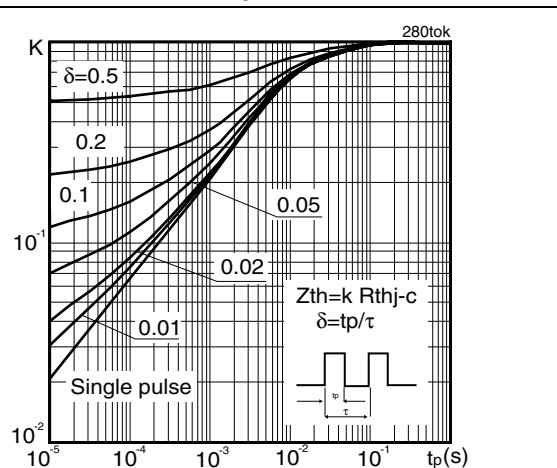


Figure 6. Output characteristics

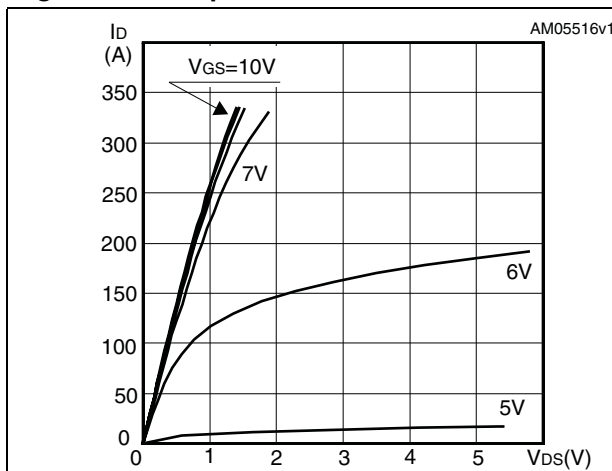


Figure 7. Transfer characteristics

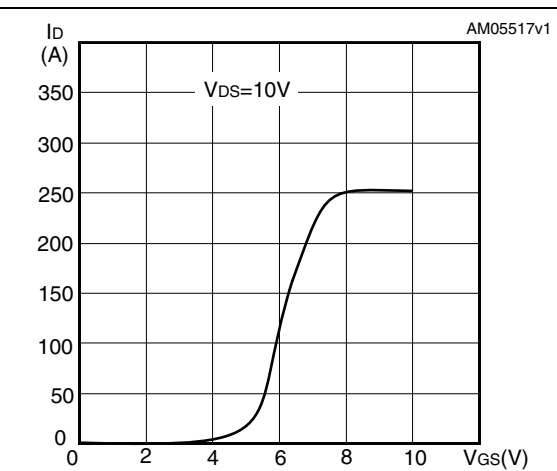


Figure 8. Normalized  $B_{VDSS}$  vs temperature

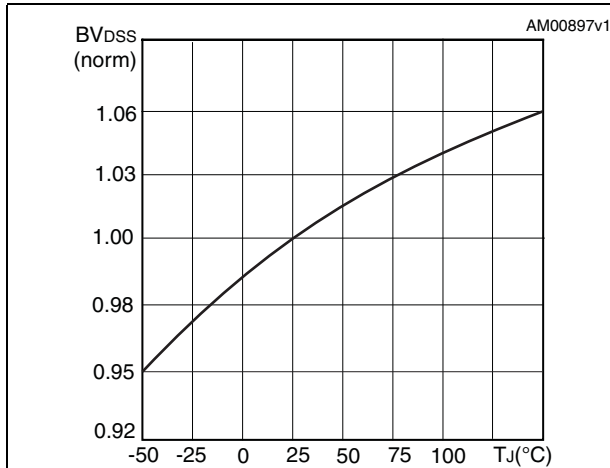


Figure 9. Static drain-source on resistance

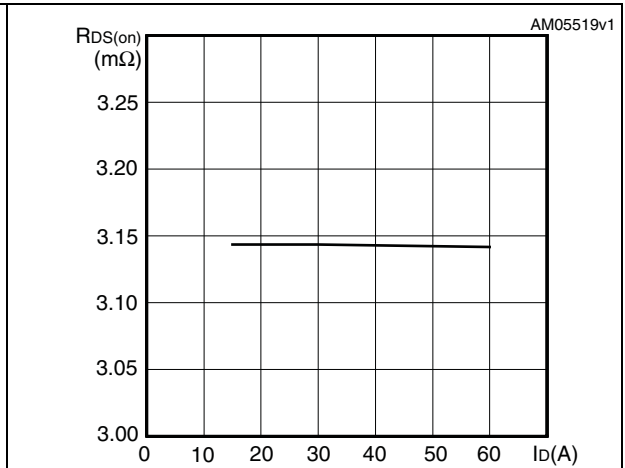


Figure 10. Gate charge vs gate-source voltage

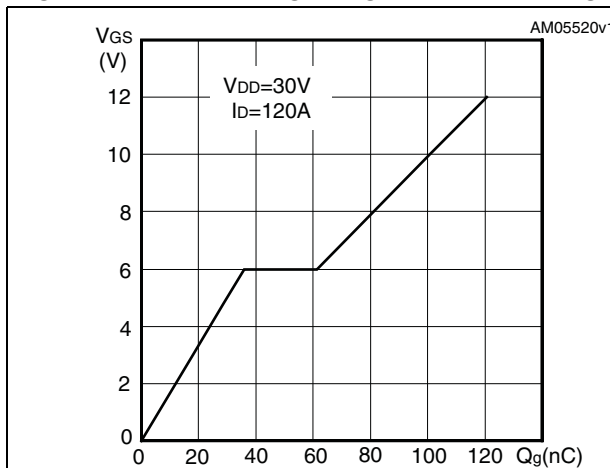


Figure 11. Capacitance variations

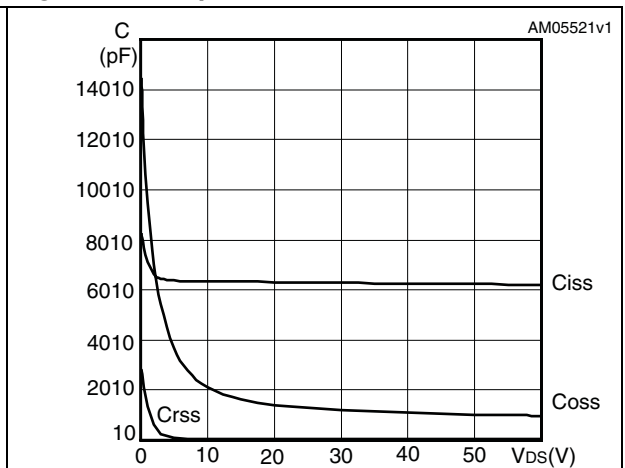


Figure 12. Normalized gate threshold voltage vs temperature

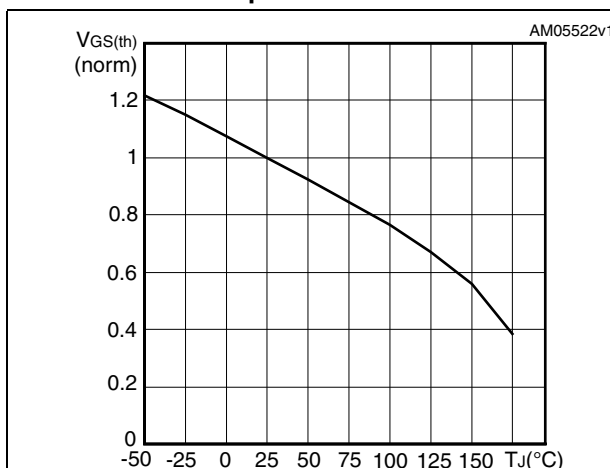


Figure 13. Normalized on resistance vs temperature

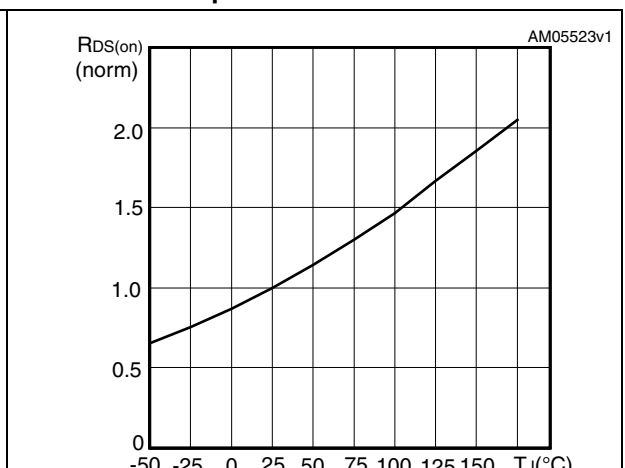
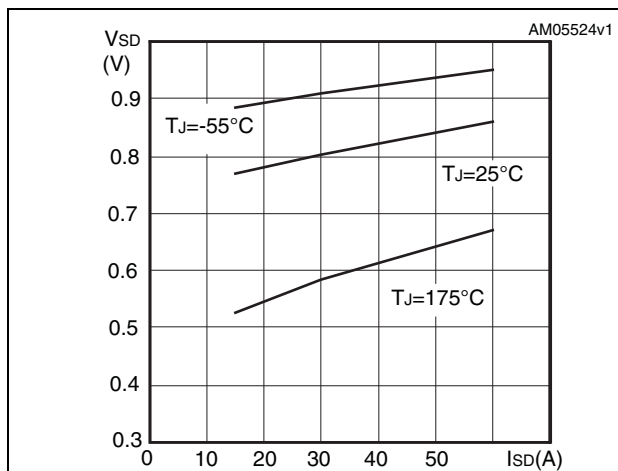


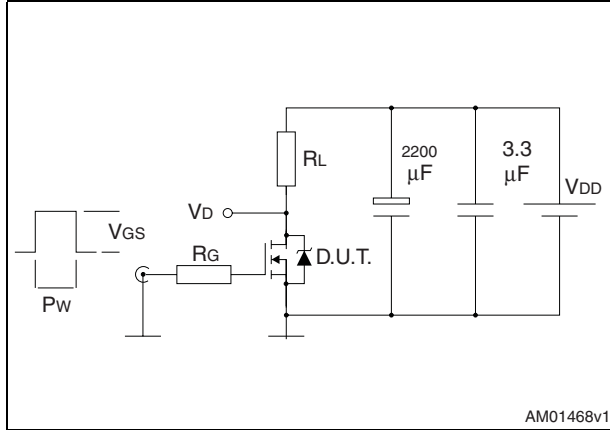
Figure 14. Source-drain diode forward characteristics



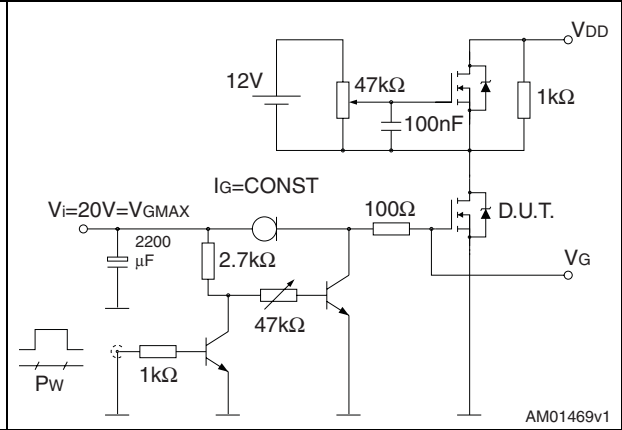


### 3 Test circuits

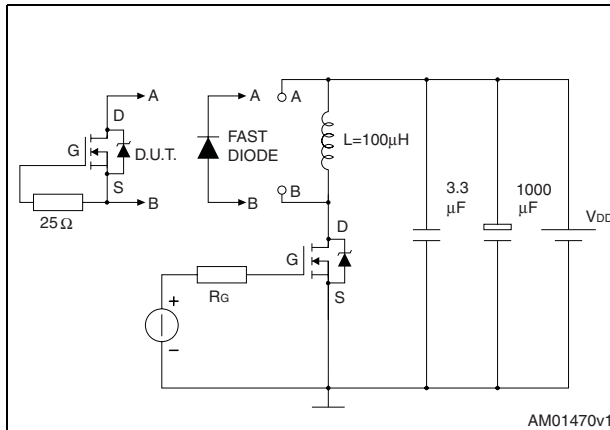
**Figure 15. Switching times test circuit for resistive load**



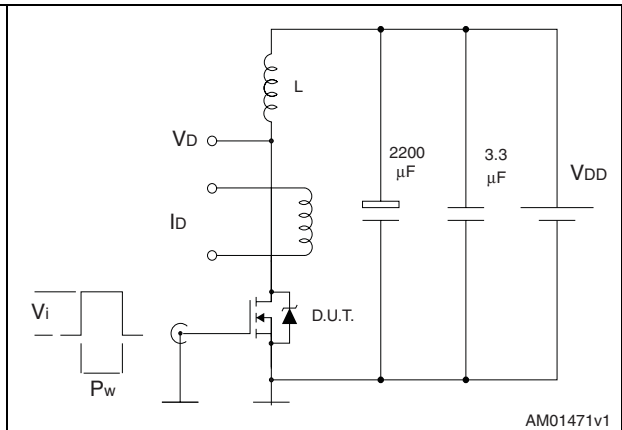
**Figure 16. Gate charge test circuit**



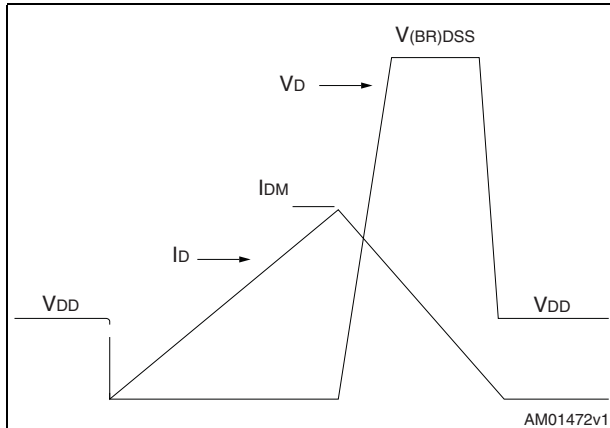
**Figure 17. Test circuit for inductive load switching and diode recovery times**



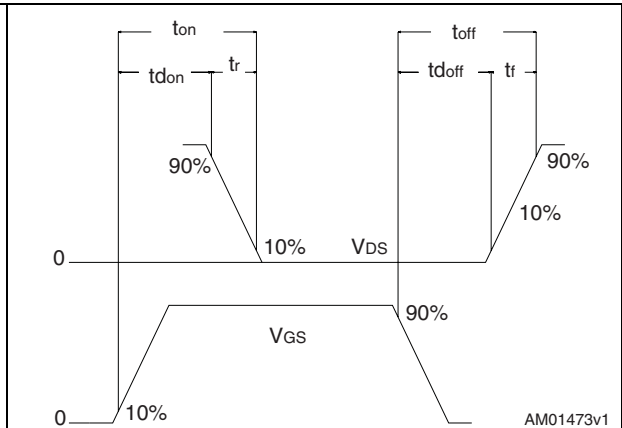
**Figure 18. Unclamped inductive load test circuit**



**Figure 19. Unclamped inductive waveform**



**Figure 20. Switching time waveform**

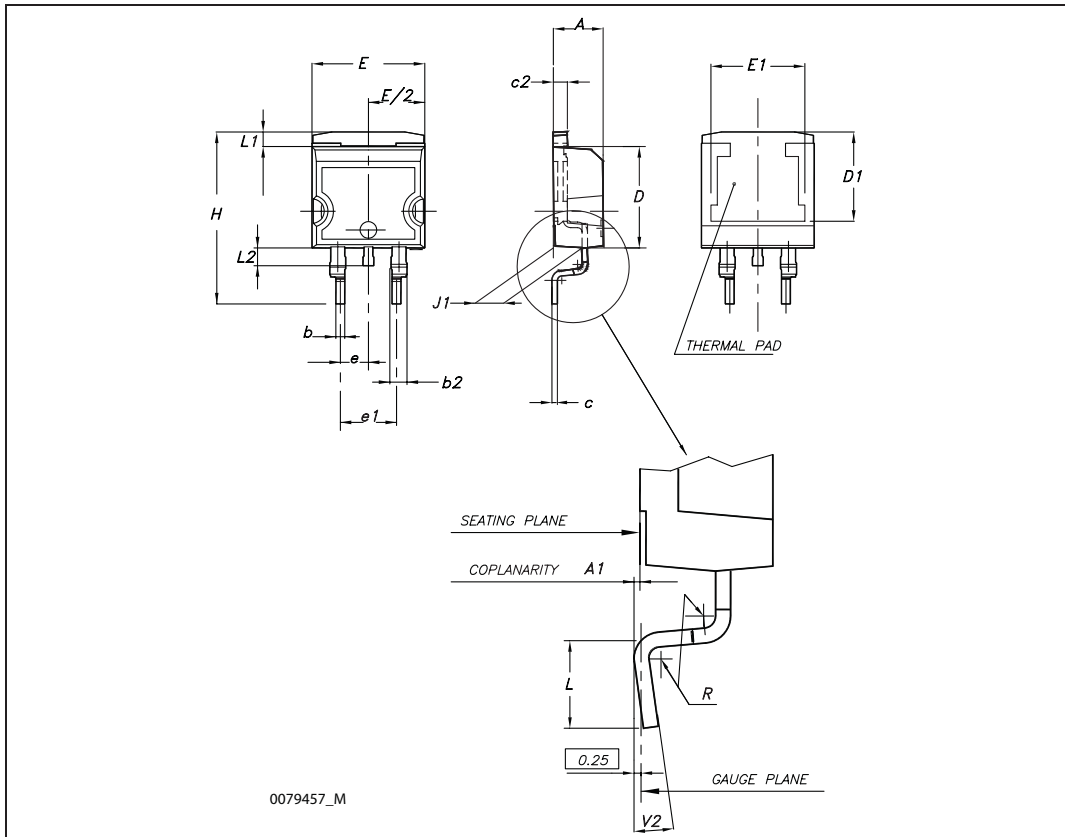


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

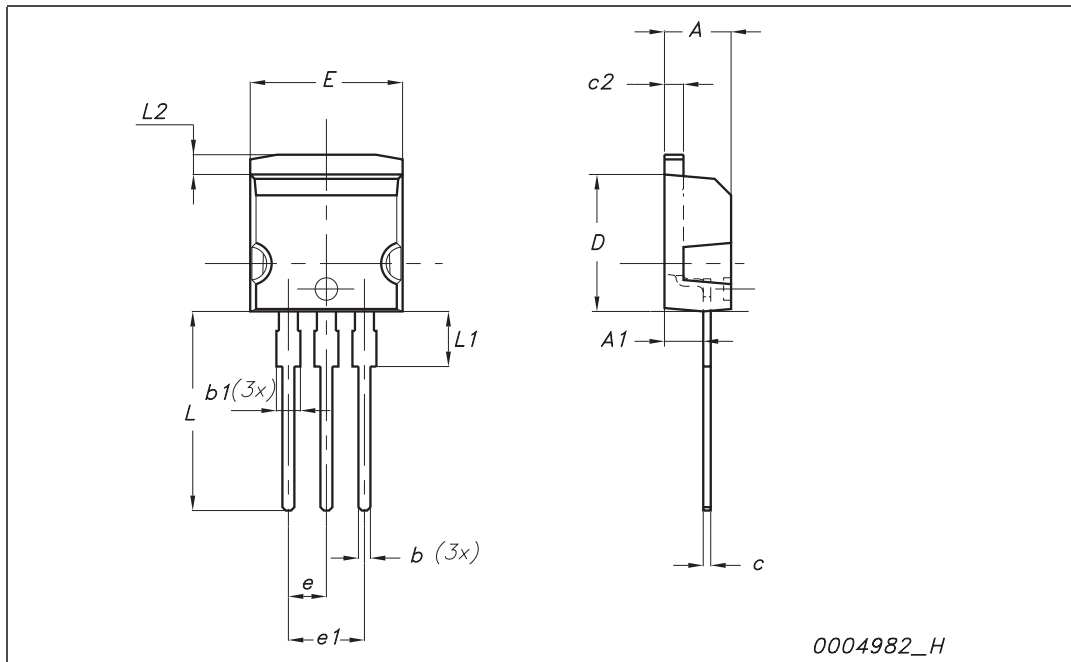
D<sup>2</sup>PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



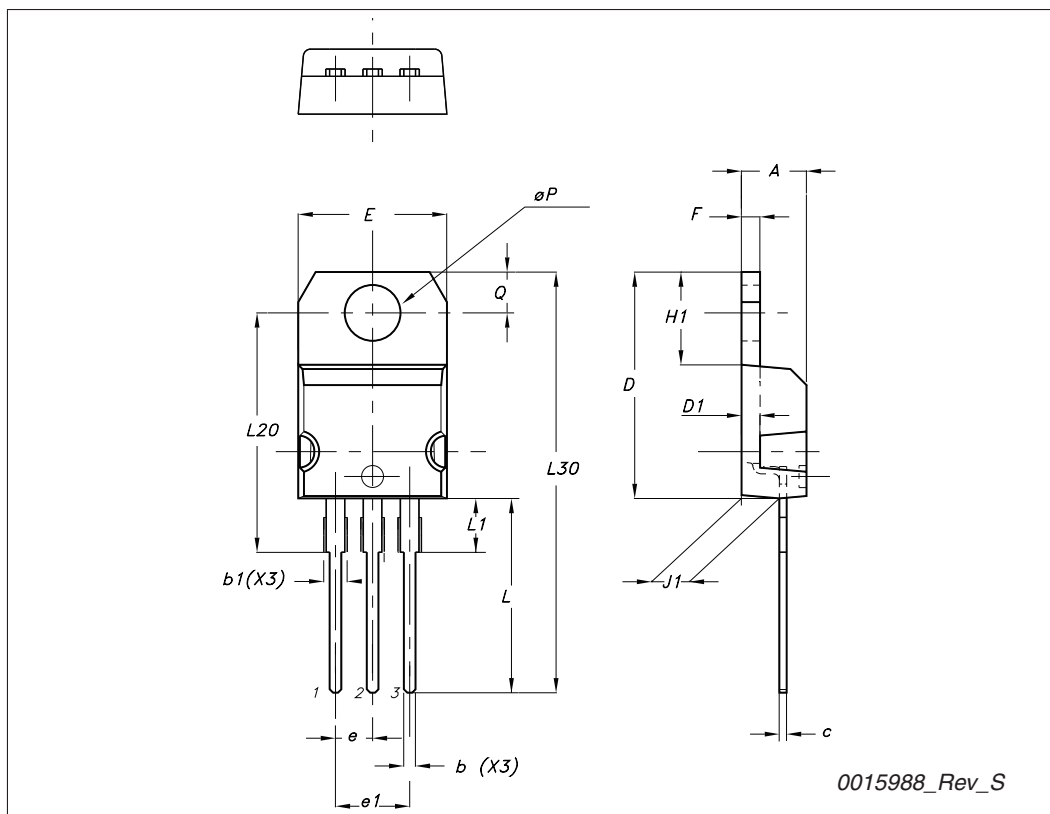
I<sup>2</sup>PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



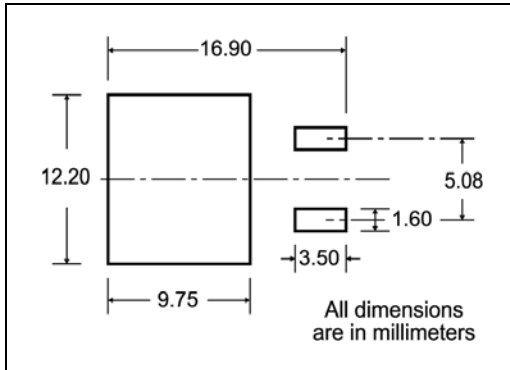
## TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



# 5 Packaging mechanical data

## D<sup>2</sup>PAK FOOTPRINT



## TAPE AND REEL SHIPMENT

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

10 pitches cumulative tolerance on tape +/- 0.2 mm

\* on sales type

## 6 Revision history

**Table 7. Document revision history**

<b>Date</b>	<b>Revision</b>	<b>Changes</b>
20-Apr-2009	1	First version.
18-Nov-2009	2	Document status promoted from preliminary data to datasheet.

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